

40V P-Channel Enhancement Mode MOSFET

Voltage -40

-40 V

Current

-46 A

Features

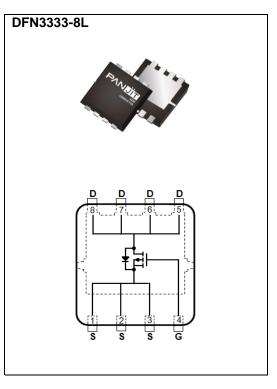
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_{D}@-10A<12m\Omega$
- R_{DS(ON)}, V_{GS}@-4.5V, I_D@-8A<17.5mΩ
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-40	.,,	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	Tc=25°C	- I _D	-46		
	T _C =100°C		-29	Α	
Pulsed Drain Current(Note 1)	Tc=25°C	I _{DM}	-166		
Power Dissipation	T _C =25°C	D	59.5	W	
	Tc=100°C	Pb	23		
Continuous Drain Current(Note 4)	T _A =25°C	Ι _D	-8.8	^	
	T _A =70°C		-7.1	Α	
Power Dissipation	T _A =25°C	Б	2.1	W	
	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	Rejc	2.1	°C/W	
	Junction to Ambient	$R_{\theta JA}$	59.5		

• Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.52	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-10A	-	10	12	mΩ
		V _{GS} =-4.5V, I _D =-8A	-	13.5	17.5	mt2
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 6)			_			
Total Gate Charge	Qg	V _{DS} =-32V, I _D =-10A,	-	23	-	nC
Gate-Source Charge	Qgs		-	8.5	-	
Gate-Drain Charge	Q_{gd}	VGS=-4.5 V(1818 2,8)	-	9	-	
Input Capacitance	Ciss	\/ OF\/ \/ O\/	-	2767	-	pF
Output Capacitance	Coss	V _{DS} =-25V, V _{GS} =0V, f=1MHZ	-	247	-	
Reverse Transfer Capacitance	Crss	I=IIVIDZ	-	139	-	
Turn-On Delay Time	td _(on)		-	23	-	
Turn-On Rise Time	t _r	V _{DS} =-20V, I _D =-1A,	-	10	-	ns
Turn-Off Delay Time	td _(off)	V _{GS} =-10V, R _G =6 Ω	-	135	-	
Turn-Off Fall Time	t _f	(100 2,0)	-	50	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	-46	А
Diode Forward Current	I _S					
Diode Forward Voltage	V _{SD}	Is=-1A, V _{GS} =0V	_	-0.7	-1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

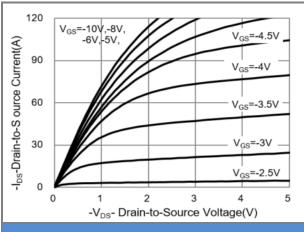


Fig.1 On-Region Characteristics

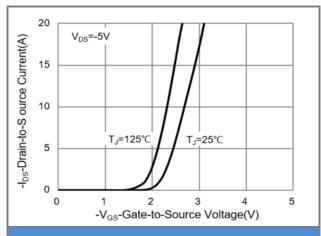


Fig.2 Transfer Characteristics

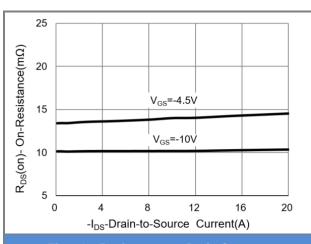


Fig.3 On-Resistance vs. Drain Current

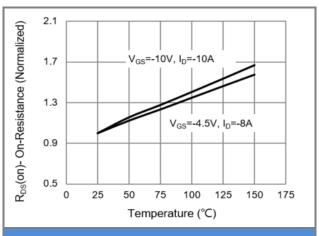


Fig.4 On-Resistance vs. Junction temperature

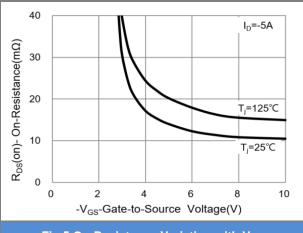


Fig.5 On-Resistance Variation with V_{GS}

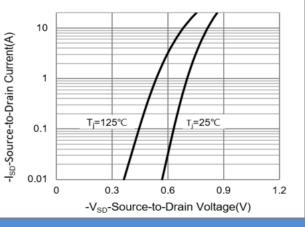


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

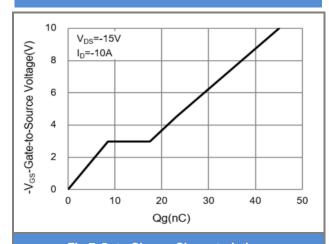


Fig.7 Gate-Charge Characteristics

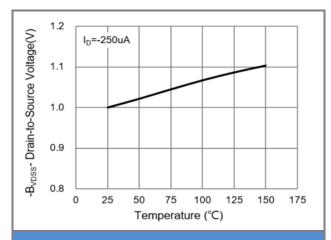


Fig.8 Breakdown Voltage Variation vs. Temperature

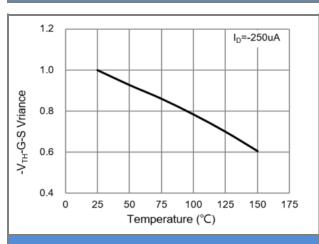


Fig.9 Threshold Voltage Variation with Temperature

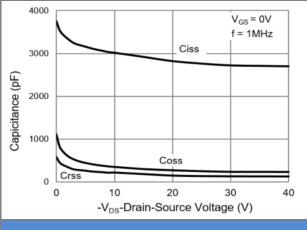
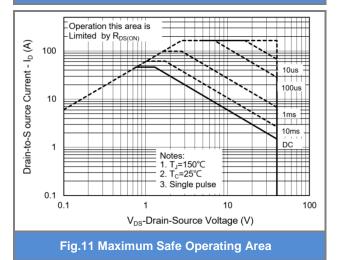


Fig.10 Capacitance vs. Drain-Source Voltage



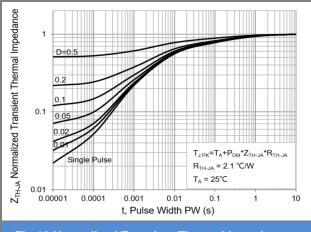


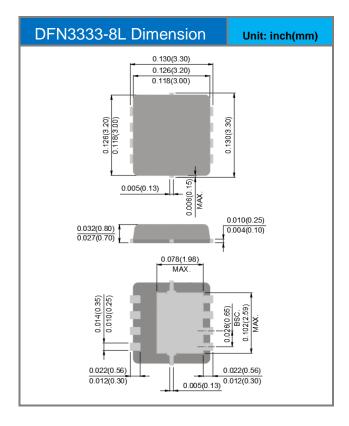
Fig.12 Normalized Transient Thermal Impedance

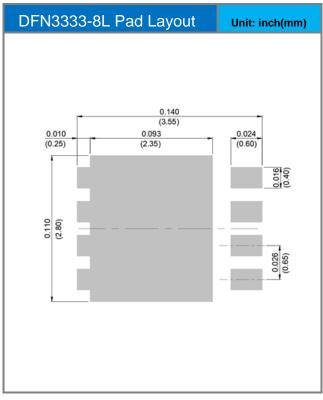


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ4443P-AU	DFN3333-8L	5K pcs / 13" reel	4443

Packaging Information & Mounting Pad Layout







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